	L #	Hits	Search Text	DBs
1	L1	303214	"257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	L2	1398	1 and (MISFET? or (metal near insulator near semiconductor near transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	L3	14	2 and (different near thickness) near (gate near insulat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	L4	1103	(furukawa-ryoichi or sakai-satoshi or yamamoto-satoshi).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	L5	11	4 and (MISFET? or (metal near insulator near semiconductor near transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	L6	2	5 and (different near thickness) near (gate near insulat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	L7	258	(MISFET? or (metal near insulator near semiconductor near transistor)).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	L8	18	7 and (gate near (oxide or insulat$3)).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	L9	2793	(MISFET? or (metal near insulator near semiconductor near transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	L10	106	9 and ((different near thickness) or (thick and thin)) near (gate near (oxide or insulat$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
11	L11	18	10 and (SiON or (silicon near oxynitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
12	L12	14	11 and (metal near oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	L13	3	12 and interface near (oxide or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB